

Design For Yield (DFY) Concepts for Analogue and Mixed-Signal Circuits

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Overview

- Circuit DfY in the design flow
- Application examples
- Worst-case Analysis and Diagnosis
- Comparison to digital corners and Monte Carlo
- Operating conditions and Yield
- Mismatch in analog circuits
- Summary: What's special about analog DfY ?

Field of Application

- Application: Full-custom circuit design at the transistor level
 - Analog & Mixed signal (A/MS) cells like operational amplifier, filter, PLL
 - Digital library optimization, full custom logic
 - Memory
- Where in the design flow?
 - Sizing of transistor geometries (after topology selection, before layout)
 - Analysis and compensation of parasitic influences in extracted view (after layout)
- Goals
 - Performance
 - Robustness against parametric process variation and operating conditions

WiCkeD Applied to Customer Circuits and Technologies

Circuits:

- Adiabatic Logic Gates
- Bandgaps
- Buffer chains
- Bypass Filters
- Cascode Gain Stages
- CCOs
- Charge Pumps
- CML Converters
- Comparators
- Constant Voltage Sources
- Current Mirrors
- Current Sources
- Current Mirror OpAmps
- Differential Amplifiers
- Filters
- Folded-Cascode OpAmps
- Fully Differential OpAmps
- High Voltage Circuits
- Latches
- Level Shifters
- Low Voltage Circuits
- Operational Amplifiers
- PLLs
- Receivers
- RF-Circuits
- Ring Oscillators
- Sense Amplifiers
- Sensor Circuits
- Single-Stage Amplifiers
- Transceivers
- VCOs

Technologies:

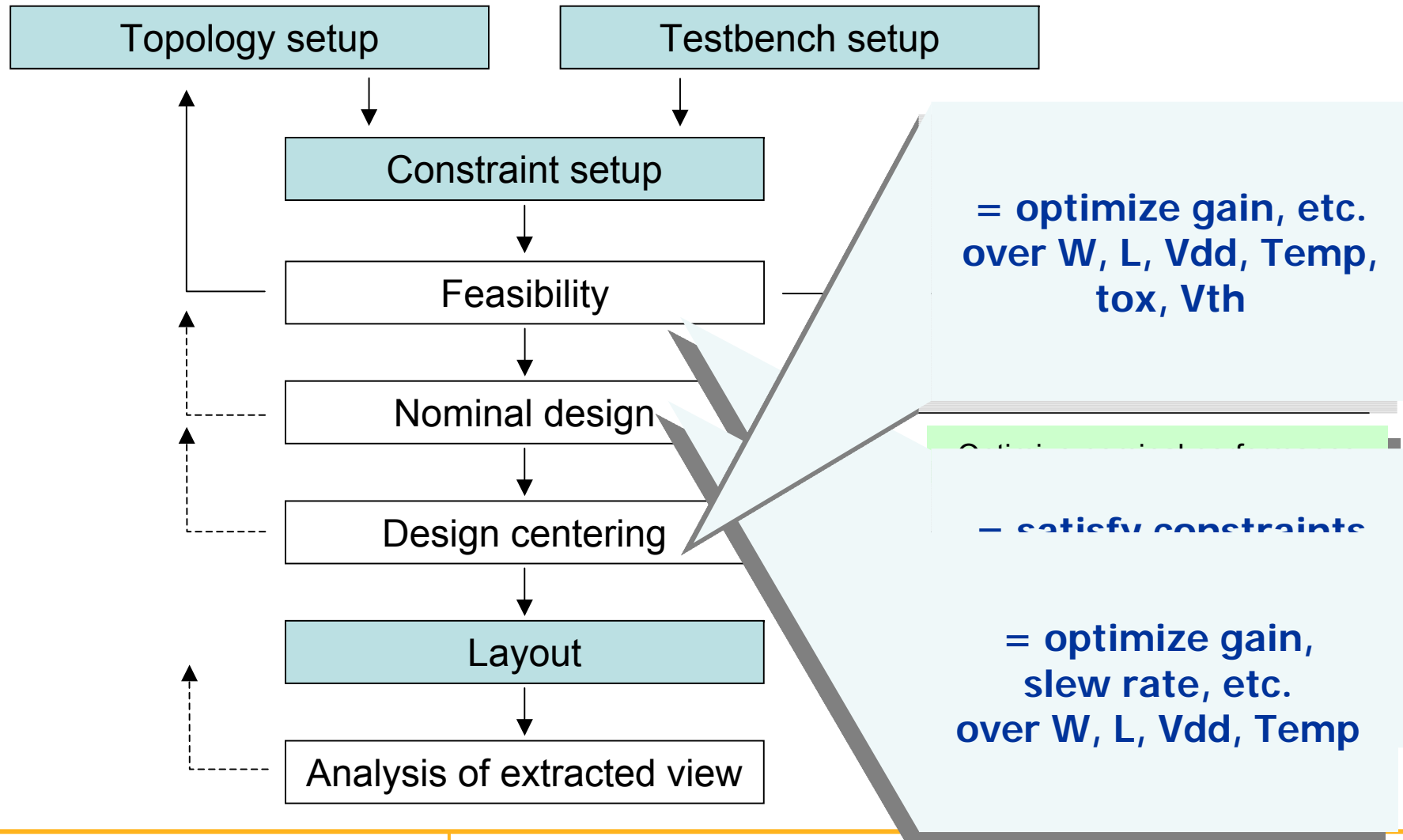
- From 1 μ down to 90n CMOS
- Projects in 65n CMOS started
- BiCMOS, BCD, Bipolar...

Applications:

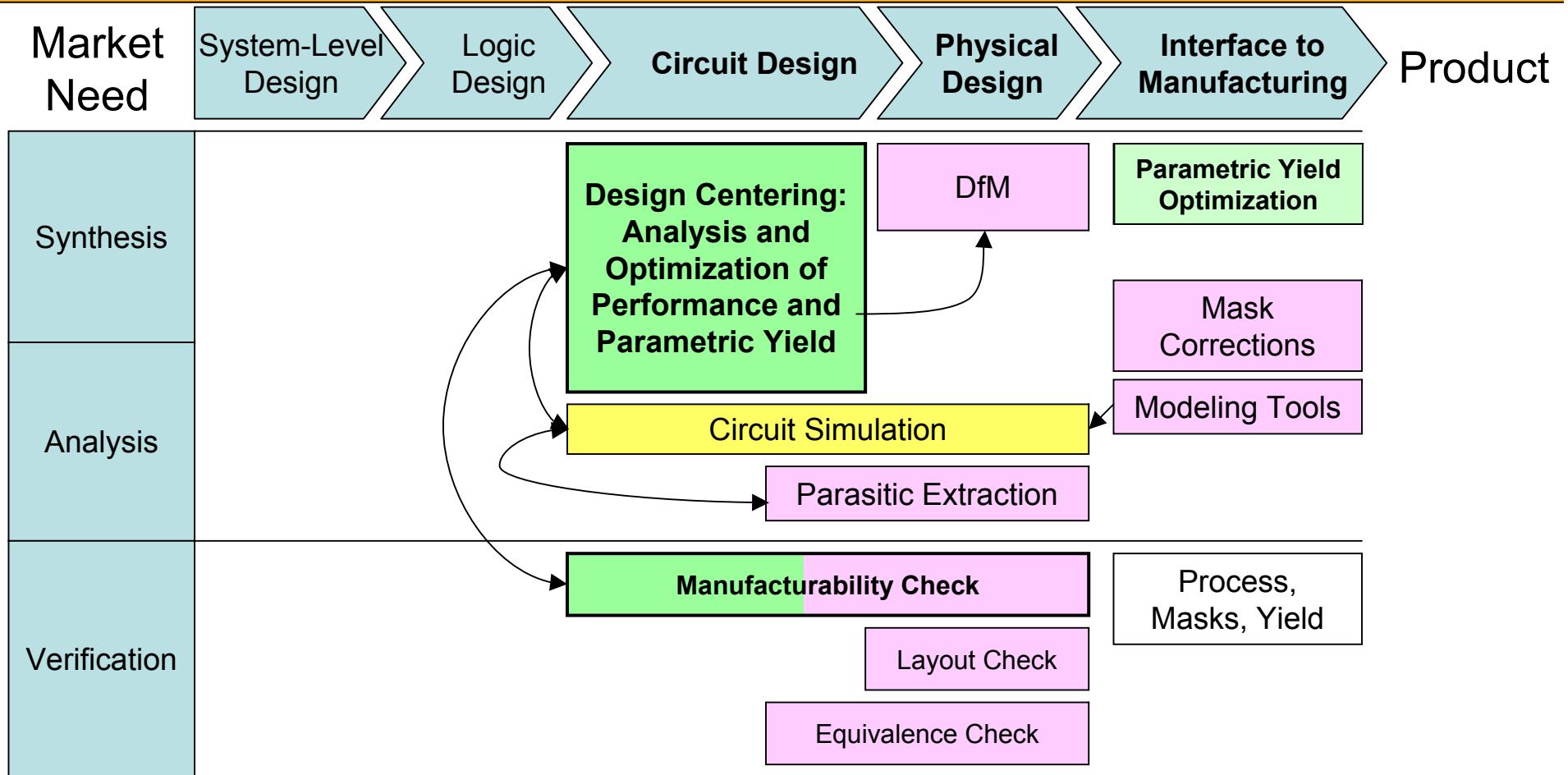
- Memory
- Wireless Communications
- Wirebound Communications
- Automotive & Industrial
- Sensors
- Consumer & Standard ICs...

More than 250 design projects since 2002

Workflow with WiCkeD



DFM/DFY - Design Centering and Yield Optimization in the AMS/RF Flow



Source: SIA ITRS 2003

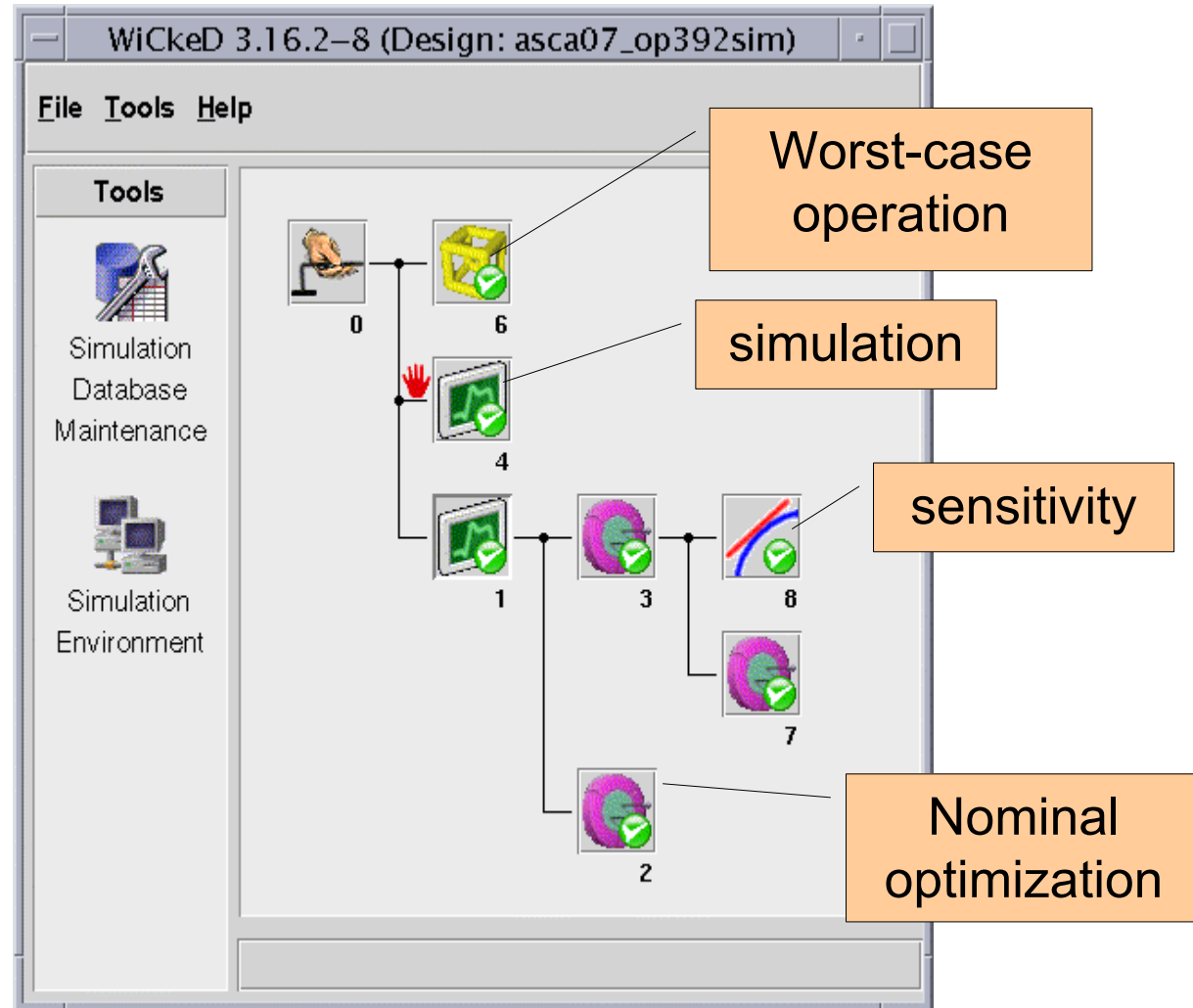
Circuit Simulation

Layout, DfM, Physical Design

Design Centering / Yield Optimization

WiCkeD Main window (example)

The history tree grows from top left to bottom right



Three parameter spaces

- **Design parameters**

- for instance widths and lengths of transistors
- are adjustable by the designer

d

- **Process parameters**

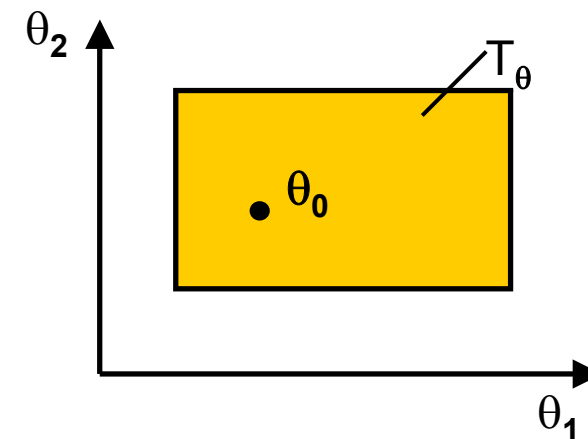
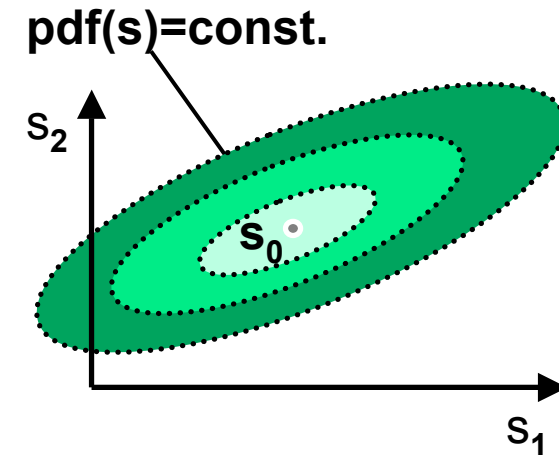
- for instance t_{ox} , v_{th}
- global and local (mismatch)
- random variation

s

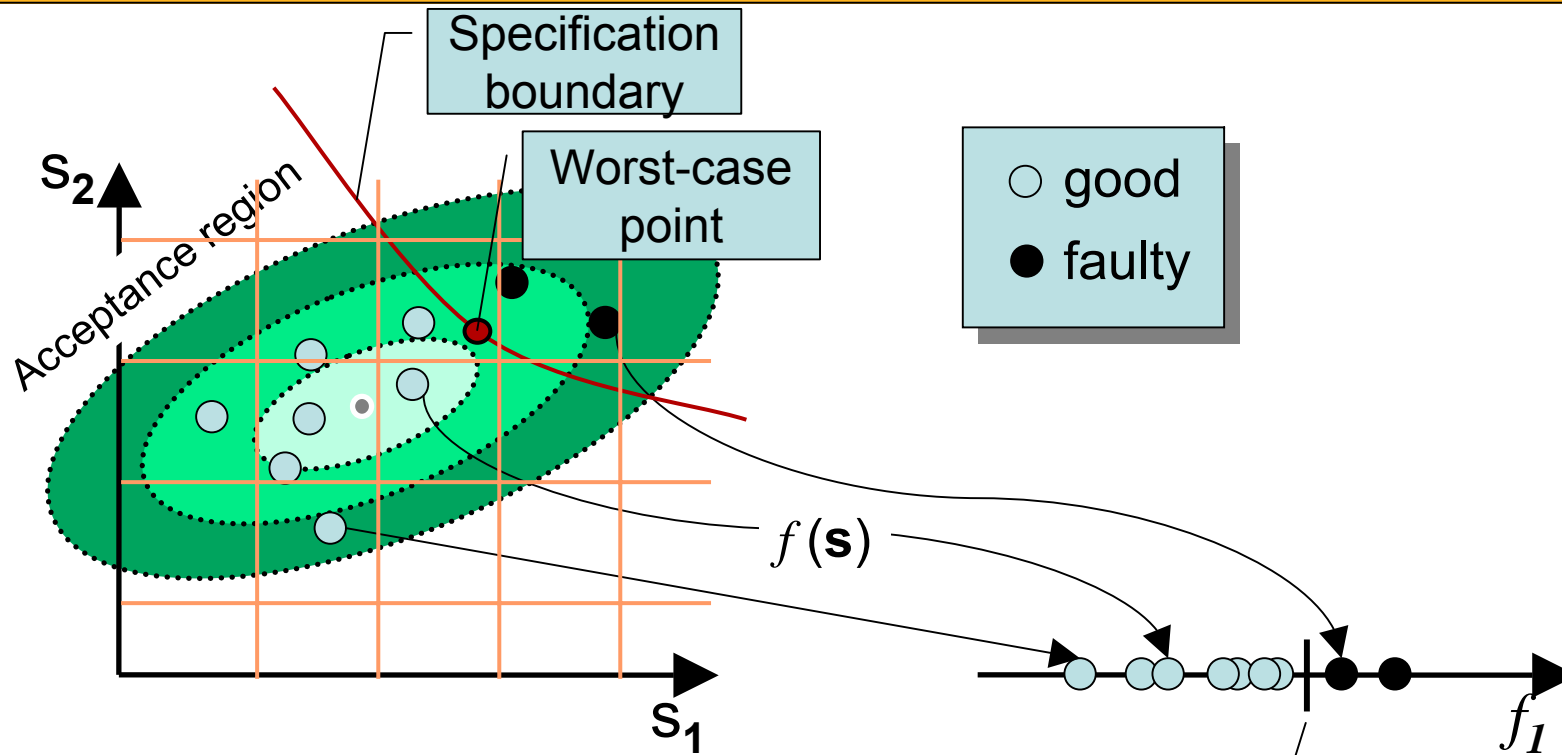
- **Operating parameters**

- for instance v_{dd} , temperature
- range of operating conditions

θ

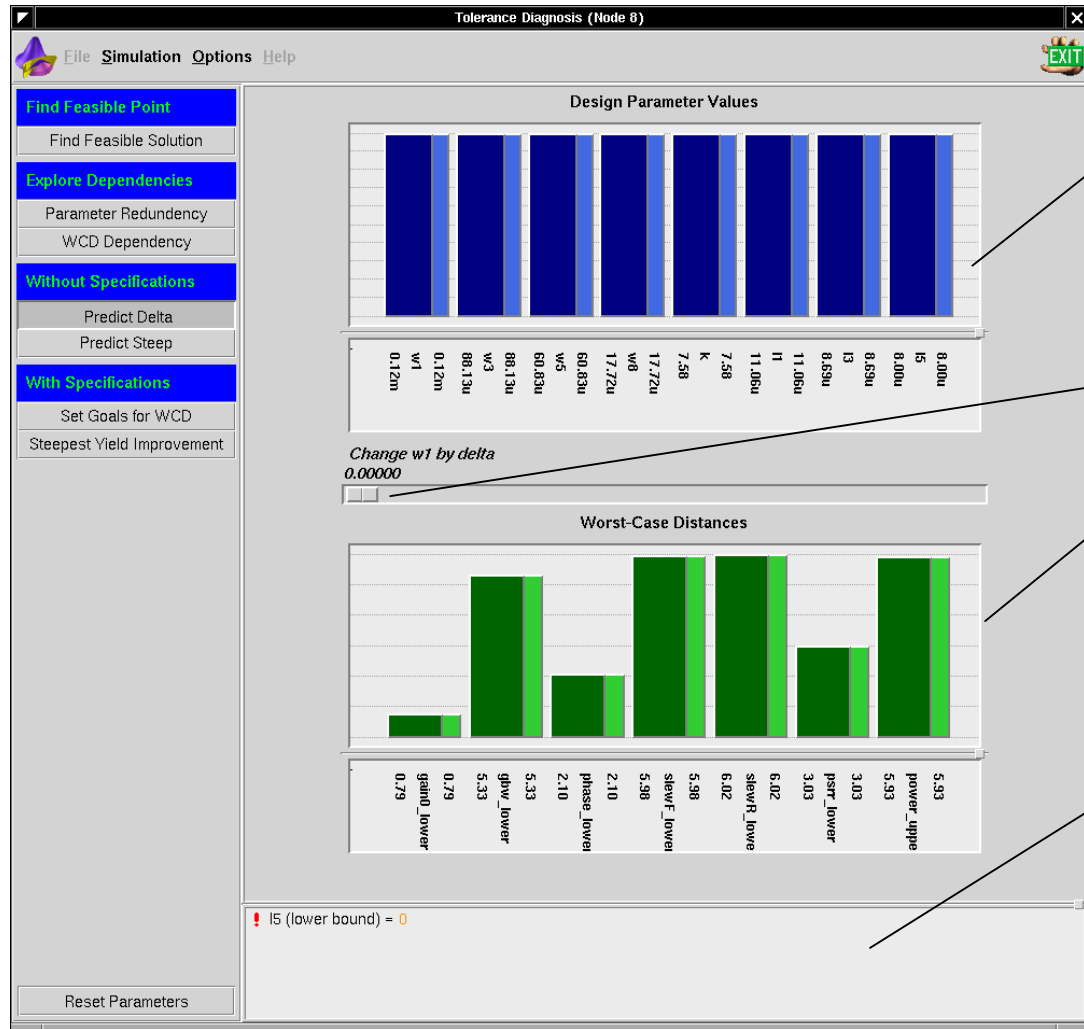


Worst-case point



The worst-case point is the parameter set of highest probability density that a parametric fault occurs.

Worst-case Diagnosis



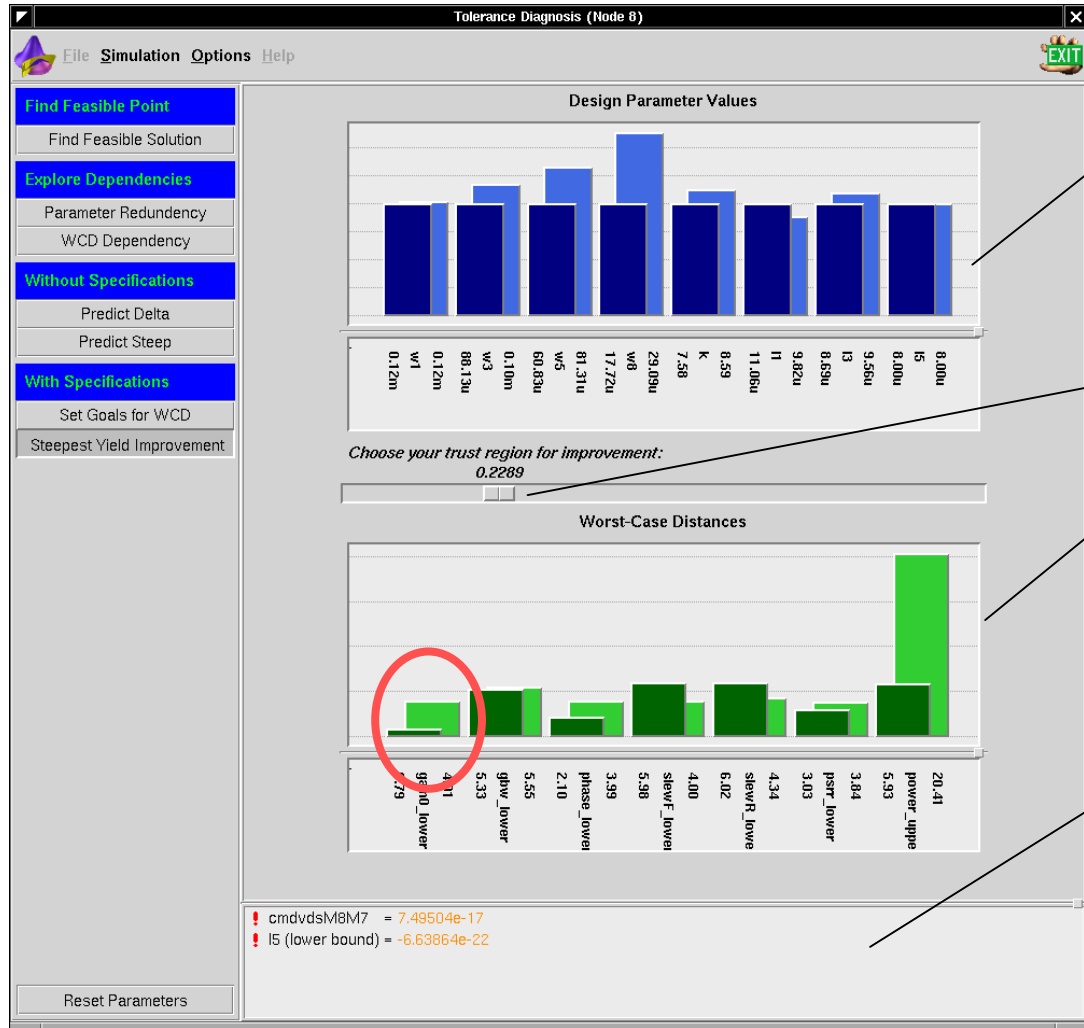
parameters

change slider

worst-case distances

constraints

Worst-case Diagnosis



parameters

change slider

worst-case distances

constraints

Worst-case points vs. digital corners vs. Monte Carlo

	WCD	S/F Corner	Monte Carlo
reflects technology	✓	✓	✓
topology dependent	✓	⊘	✓
analog performances	✓	⊘	✓
yield estimation	✓	⊘	✓
mismatch	✓	⊘	✓
yield improvement	✓	⊘	⊘
efficiency	+	++	--

Monte Carlo-Analysis incl. Operating Conditions

operating parameter

T [°C]

T_{max}

T_{min}

t_{ox,min}

t_{ox,max}

Y = 45%

Spec: A₀ > 80 dB
for all

T_{min} < T < T_{max}

A₀(t_{ox}, T) < 80 dB

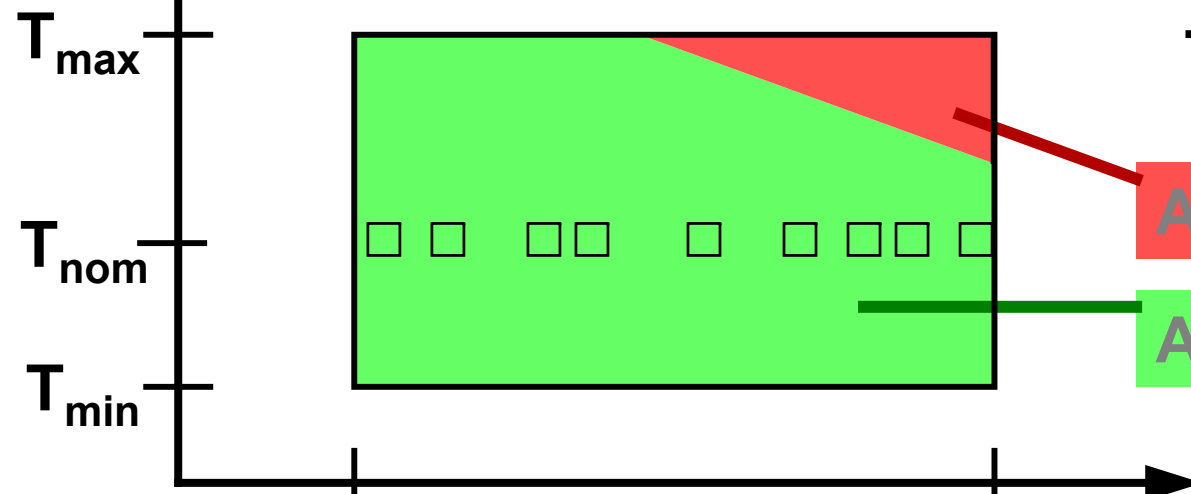
A₀(t_{ox}, T) > 80 dB

process parameter
t_{ox} [μm]

Monte Carlo-Analysis incl. Operating Conditions

operating parameter

T [°C]



Spec: $A_0 > 80$ dB
for all

$T_{min} < T < T_{max}$

$A_0(t_{ox}, T) < 80$ dB

$A_0(t_{ox}, T) > 80$ dB

$t_{ox,min}$

$t_{ox,max}$

process parameter

t_{ox} [μm]

$Y_{est} = 100\%$
wrong

Monte Carlo-Analysis incl. Operating Conditions

operating parameter

T [°C]

T_{max}

T_{min}

$t_{ox,min}$

$t_{ox,max}$

Spec: $A_0 > 80$ dB
for all

$T_{min} < T < T_{max}$

$A_0(t_{ox}, T) < 80$ dB

$A_0(t_{ox}, T) > 80$ dB

$Y_{est} = 92\%$
wrong

process parameter
 t_{ox} [μm]

Monte Carlo-Analysis incl. Operating Conditions

- Sweep over operating condition for each sample element
 - very high effort
 - For multiple operating parameters (V_{DD} , T , I_{bias} , C_{load} , ...) the effort increases exponentially
- Simulation at the worst-case operating conditions
 - is specific for each specification
- Both approaches can be combined

Monte Carlo-Analysis incl. Operating Conditions

operating parameter

T [°C]

T_{max}

T_{min}

t_{ox,min}

t_{ox,max}

Y_{est} = 45%
correct

Spec: A₀ > 80 dB
for all

T_{min} < T < T_{max}

A₀(t_{ox}, T) < 80 dB

A₀(t_{ox}, T) > 80 dB

process parameter
t_{ox} [μm]

Monte Carlo-Analysis of A₀ over t_{ox} at T = T_{max}

Monte Carlo-Analysis incl. operating conditions

Samples in (t_{ox}, v_{th}) **Example:**

Simulation of

$A_0(t_{ox}, v_{th})$	for T_{max}, VDD_{min}
$Ft(t_{ox}, v_{th})$	for T_{min}, VDD_{min}
Power (t_{ox}, v_{th})	for T_{max}, VDD_{max}

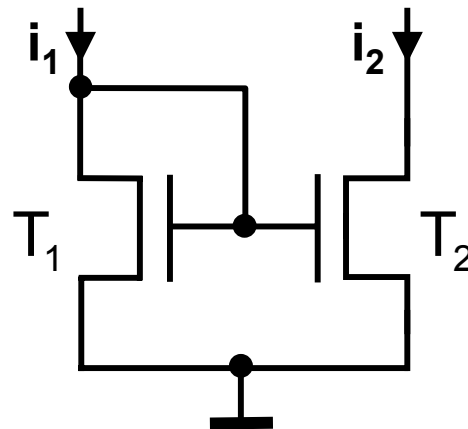


distributions, moments, ...
Partial yields $Y_{A_0}, Y_{Ft}, Y_{Power}$
Total yield Y

Mismatch

- Analog circuits are based on symmetries
- Mismatch = asymmetry caused by local variation

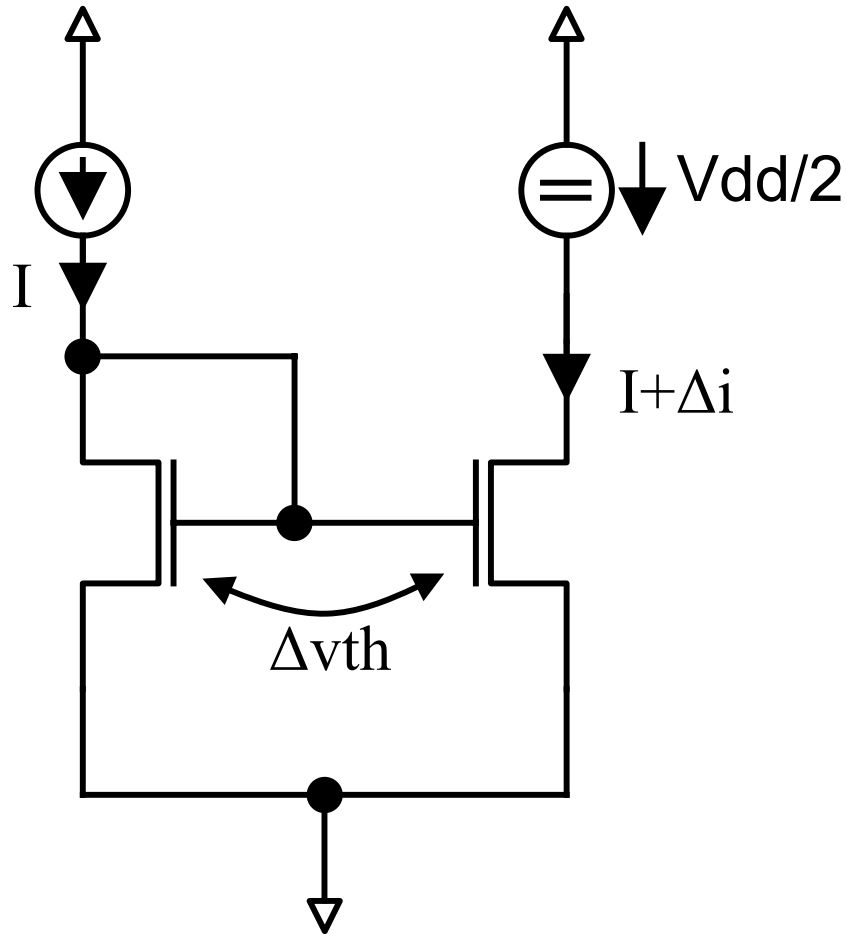
Example:
Current mirror



$$i_2 = k \left(\sqrt{\frac{i_1}{k}} + \underbrace{V_{th1} - V_{th2}}_{\Delta V_{th}} \right)^2$$

Mismatch: $\Delta V_{th} \neq 0 \Leftrightarrow i_2 \neq i_1$

Current Mirror: „small signal“ mismatch



$$\Delta i = g_m \cdot \Delta v_{th}$$

$$\sigma_{\Delta i} = g_m \cdot \sigma_{\Delta v_{th}}$$

Mismatch Influence

$$\sigma_{\Delta i} = g_m \cdot \sigma_{\Delta v_{th}}$$

Biasing:

$$I = k \frac{W}{L} (V_{gs} - V_{th})^2$$

$$g_m = \frac{\partial I}{\partial V_{gs}} = 2k \frac{W}{L} (V_{gs} - V_{th})$$

$$= 2\sqrt{k} \sqrt{\frac{W}{L}} I$$

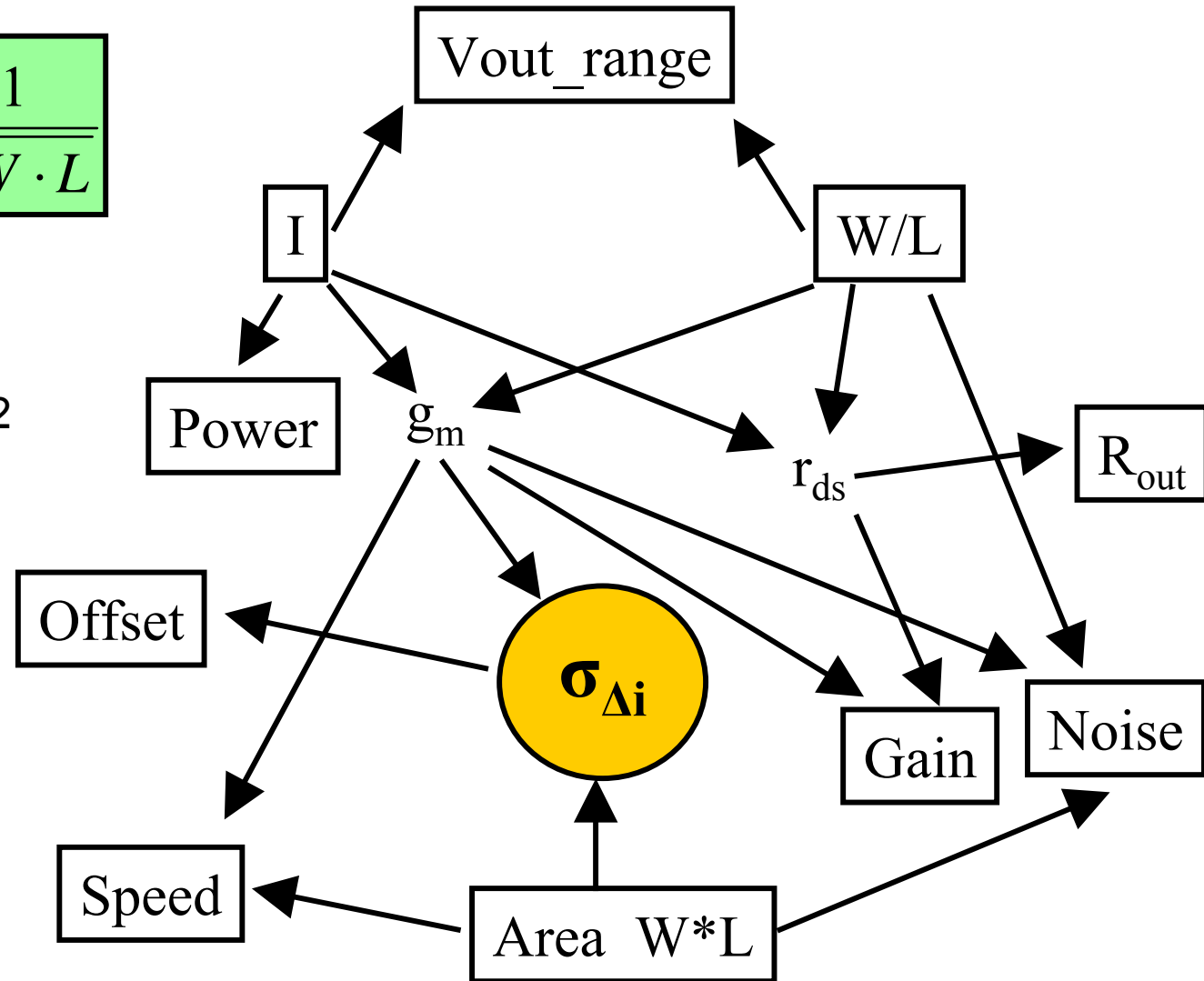
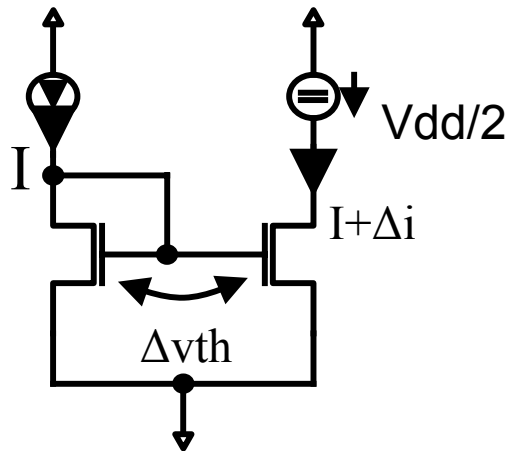
Pelgrom's Area Law:

$$\sigma_{\Delta v_{th}} = \frac{A_{mm}}{\sqrt{W \cdot L}}$$

$$\sigma_{\Delta i} \propto \sqrt{\frac{W}{L}} \cdot \sqrt{I} \cdot \frac{1}{\sqrt{W \cdot L}} = \frac{\sqrt{I}}{L}$$

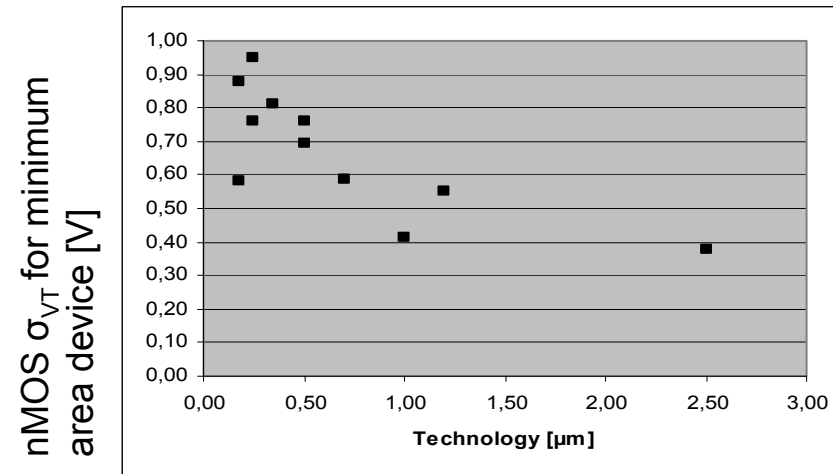
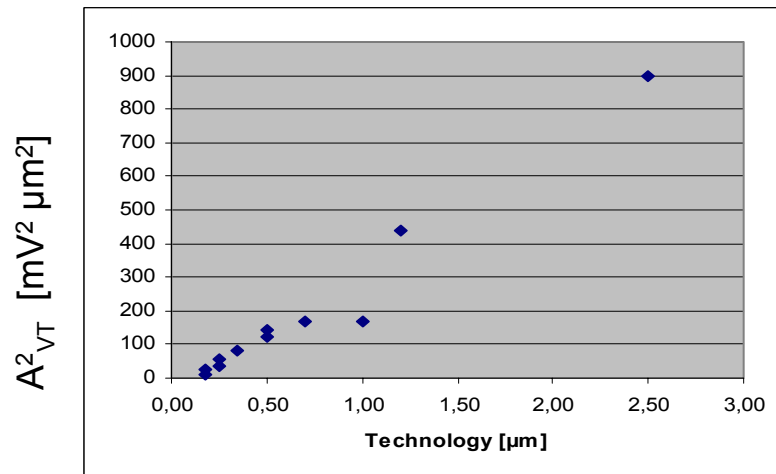
Mismatch Tradeoffs

$$\sigma_{\Delta i} \propto \sqrt{\frac{W}{L}} \cdot \sqrt{I} \cdot \frac{1}{\sqrt{W \cdot L}}$$



Mismatch (3)

- Variance of V_{th} depends on device area: $\sigma_{VT}^2 = A_{VT}^2 / (W \cdot L)$
- Problem grows with scaling:
 - A_{VT}^2 decreases only linearly with the minimum feature size, therefore the variance of the minimum area device grows
 - Decreasing V_{dd} increases relative error $\sigma_{VT} / V_{in RMS}$
- Analog circuits cannot be simply scaled.



Source: Peter R. Kinget (IEEE Journal of Solid-State Circuits, 06/2005)

What's special about Analog DfY ?

- Yield of complex performances
 - ⇒ Clear separation of design, process, and operating conditions
 - ⇒ Individual worst-case points instead of pre-defined corners
- Designer's expert knowledge is important
 - ⇒ Allow strong user interaction and a design strategy
 - ⇒ Focus on analysis and incremental interactive design steps, instead of black-box „synthesis“
- Many constraints per transistor
 - ⇒ saturation, current symmetries, etc.
 - ⇒ Efficient algorithms for typical analog problem sizes